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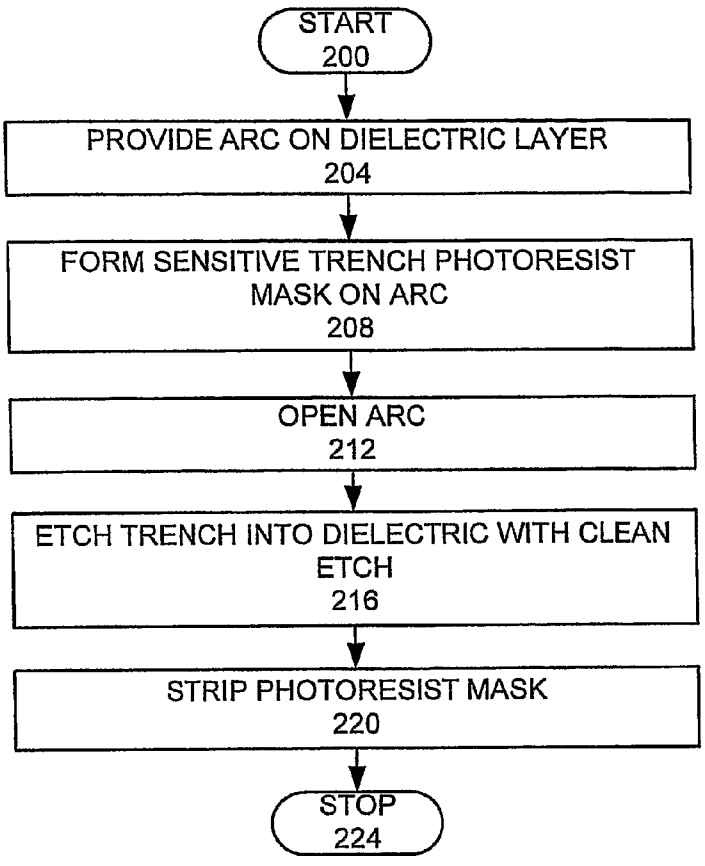
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(54) Title: LINE EDGE ROUGHNESS REDUCTION FOR TRENCH ETCH



(57) Abstract: A method for etching a trench to a trench depth in a dielectric layer over a substrate is provided. An ARC is applied over the dielectric layer. A photoresist mask is formed on the ARC, where the photoresist mask has a thickness. The ARC is etched through. A trench is etched into the dielectric layer with a dielectric to photoresist etch selectivity between 1:1 and 2:1.

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